

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application

1-5. (Canceled)

6. (Currently Amended) The method to manufacture a semiconductor device according to claim-5 9, the second through hole having a straight internal wall.

7. (Currently Amended) The method to manufacture a semiconductor device according to claim-5 9, a first size of the first through hole being the same as a second size of the second through hole.

8. (Currently Amended) The method to manufacture a semiconductor device according to claim-5 9, a first size of the first through hole being greater than a second size of the second through hole.

9. (Currently Amended) ~~The method to manufacture a semiconductor device according to claim-5, further comprising:~~ A method to manufacture a semiconductor device, comprising:

_____ preparing a semiconductor wafer including a plurality of semiconductor chip forming sections each having an electrode;

_____ forming a first through hole in the electrode;

_____ forming a second through hole penetrating the semiconductor wafer and coaxial to the first through hole, the second through hole communicating with the first through hole;

_____ forming a conduction layer that extends via the first and second through holes from a first surface of each of the semiconductor chip forming sections on which the electrode is formed to a second surface opposite to the first surface, the conduction layer being electrically connected to the electrode;

forming a dielectric film covering the electrode and an interior of the first through hole;

forming a third through hole penetrating the dielectric film, the third through hole exposing the electrode, and

the conduction layer being electrically connected to the electrode via the third through hole.

10. (Previously Presented) The method to manufacture a semiconductor device according to claim 9, further comprising:

forming a second dielectric film on an internal wall surface of the second through hole, the conduction layer being formed on the second dielectric film.

11. (Currently Amended) ~~The method to manufacture a semiconductor device according to claim 5, including the steps of:~~ A method to manufacture a semiconductor device, comprising:

_____ preparing a semiconductor wafer including a plurality of semiconductor chip forming sections each having an electrode;

_____ forming a first through hole in the electrode;

_____ forming a second through hole penetrating the semiconductor wafer and coaxial to the first through hole, the second through hole communicating with the first through hole;

_____ forming a conduction layer that extends via the first and second through holes from a first surface of each of the semiconductor chip forming sections on which the electrode is formed to a second surface opposite to the first surface, the conduction layer being electrically connected to the electrode;

forming a first dielectric film covering the electrode and an interior of the first through hole;

forming a second dielectric film on an internal wall surface of the second through hole; and

forming an opening penetrating the first and second dielectric film, the opening exposing the electrode, the conduction layer being electrically connected to the electrode via the opening.

12. (Currently Amended) The method to manufacture a semiconductor device according to claim-5 9, the first through hole being formed by a dry etching.

13. (Currently Amended) The method to manufacture a semiconductor device according to claim-5 9, the conduction layer being formed by the plating method.